

**AMENDMENTS TO THE SPECIFICATION**

Please amend paragraph 0054 as follows:

As shown in FIG. 4, an N-type nitride gallium (GaN) layer ~~102~~202 is formed on a sapphire substrate 201 and then, an N-type electrode 205 is formed at one portion of and on the N-type nitride gallium layer 202.

Please amend paragraph 0078 as follows:

After an N-type nitride gallium layer ~~[[601]]~~, an active layer, and a P-type nitride gallium layer are sequentially formed above a sapphire substrate, a P-type electrode 603 and an N-type electrode 605 are formed as shown in FIG. 8. The inventive light emitting diode has a plurality of partition regions excepting a P-type electrode 603 and an N-type electrode 605 disposed at an upper layer of the light emitting diode. Transparent electrodes 620 are disposed at the plurality of partition regions.